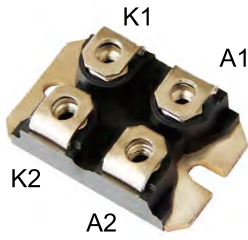
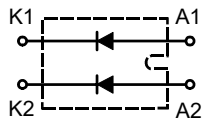
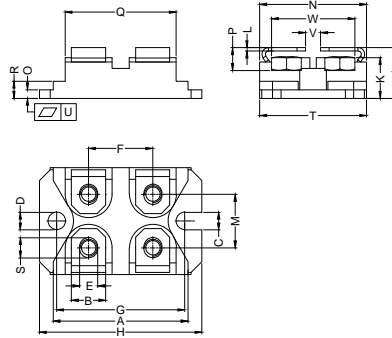


HUR2x100-120

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



Dimensions SOT -227



Dim.	Millimeter		Dim.	Millimeter	
	Min.	Max.		Min.	Max.
A	31.30	31.65	M	12.00	13.00
B	7.80	8.40	N	25.15	25.65
C	4.00	4.30	O	1.95	2.15
D	∅4.00	∅4.30	P	5.60	6.60
E	4.00	4.30	Q	25.30	26.30
F	14.90	15.20	R	3.90	4.30
G	30.10	30.30	S	4.45	4.85
H	38.00	38.50	T	24.50	25.10
J	12.10	12.90	U	0.05	0.10
K	9.00	9.60	V	3.00	4.80
L	0.75	0.85	W	19.30	20.50



	V _{RSM} V	V _{RSM} V
HUR2x100-120	1200	1200

Symbol	Test Conditions	Maximum Ratings	Unit
I _{FRMS}	T _C =60°C; rectangular, d=0.5	100	A
I _{FAVM}		100	
I _{FSM}	T _{VJ} =45°C; t _p =10ms (50Hz), sine	950	A
E _{AS}	T _{VJ} =25°C; non-repetitive; I _{AS} =3A; L=182uH	2.4	mJ
I _{AR}	V _A =1.5·V _R typ.; f=10kHz; repetitive	0.3	A
T _{VJ}		-40...+150	°C
T _{VJM}		150	
T _{stg}		-40...+150	
P _{tot}	T _C =25°C	250	W
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤1mA	2500	V~
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in.
Weight	typical	30	g



HUR2x100-120

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$ $T_{VJ}=150^{\circ}\text{C}; V_R=V_{RRM}$		1 14	mA
V_F	$I_F=100\text{A}; T_{VJ}=150^{\circ}\text{C}$ $T_{VJ}=25^{\circ}\text{C}$		1.60 1.80	V
R_{thJC} R_{thCH}	with heatsink compound	0.1	0.5	K/W
t_{rr}	$I_F=1\text{A}; -di/dt=400\text{A/us}; V_R=30\text{V}; T_{VJ}=25^{\circ}\text{C}$	40		ns
I_{RM}	$V_R=100\text{V}; I_F=200\text{A}; -di_F/dt=100\text{A/us}; T_{VJ}=100^{\circ}\text{C}$	38		A

FEATURES

- * International standard package SOT-227
- * Isolation voltage 2500 V~
- * 2 independent HiperFRED in 1 package
- * Planar passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM} -values
- * Soft recovery behaviour
- * UL File NO.E310749
- * RoHS compliant

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * Avalanche voltage rated for reliable operation
- * Soft reverse recovery for low EMI/RFI
- * Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch



ORDERING INFORMATION

Part Number	Package	Shipping	Marking Code
HUR2X100-120	SOT-227	10pcs / Tube	HUR2X100-120

HUR2x100-120

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

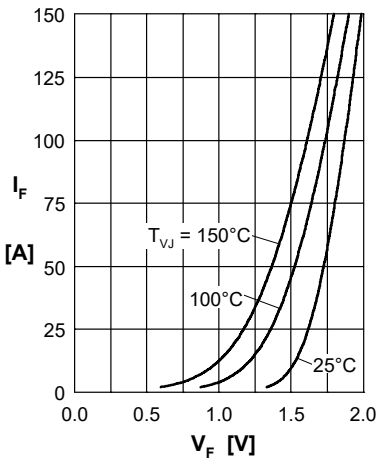


Fig. 1 Forward current I_F versus V_F

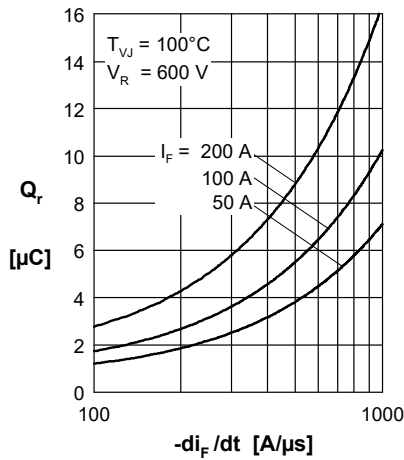


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

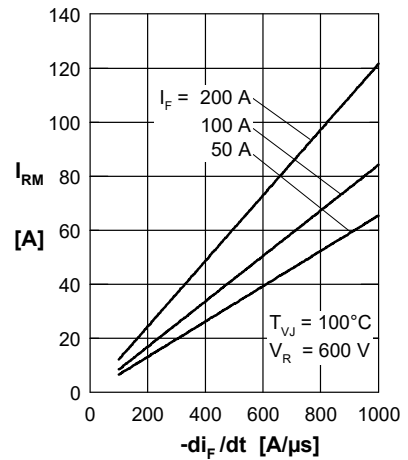


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

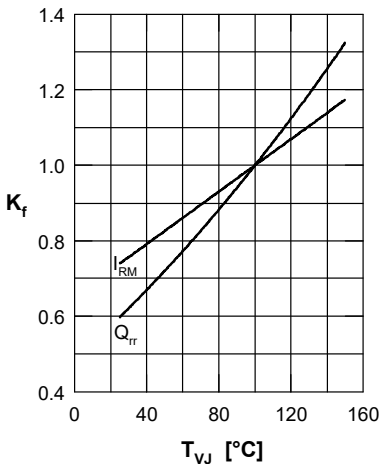


Fig. 4 Dyn. parameters Q_{rr} , I_{RM} versus T_{VJ}

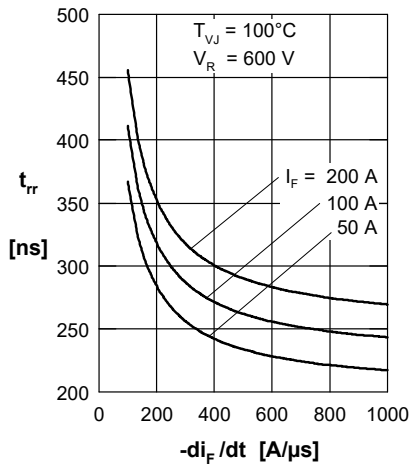


Fig. 5 Typ. recovery time t_{tr} versus $-di_F/dt$

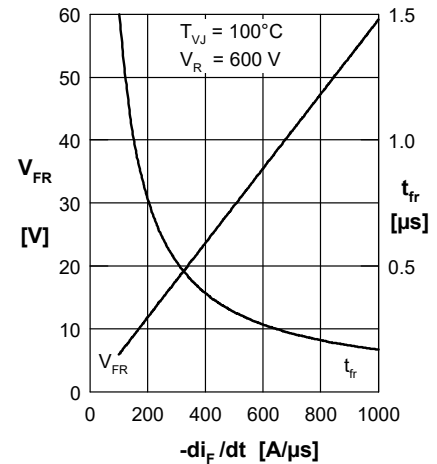


Fig. 6 Typ. peak forward voltage V_{FR} and t_{tr} versus di_F/dt

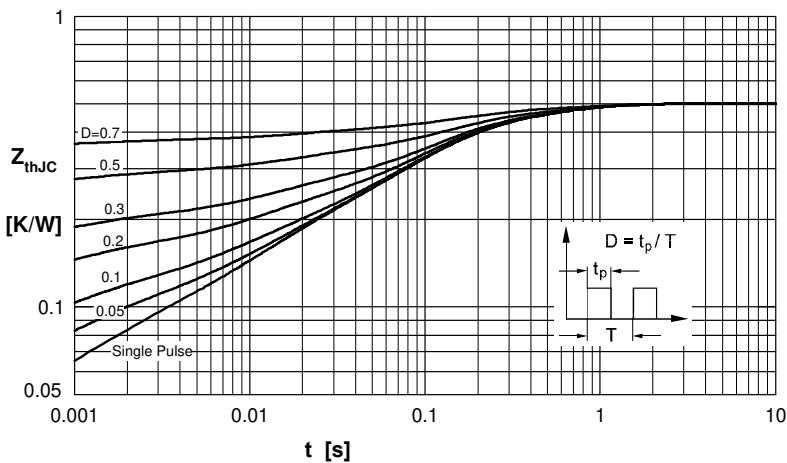


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thjC} calculation:

i	R_{thi} [K/W]	t_i (s)
1	0.020	0.00002
2	0.050	0.00081
3	0.076	0.01000
4	0.240	0.09400
5	0.114	0.45000